

Technical Data
Data Sheet 2910, Rev. A

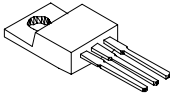
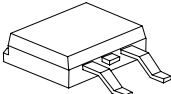
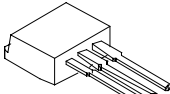
MBR25..CT/ MBRB25..CT/ MBR25..CT-1
SCHOTTKY RECTIFIER

Applications:

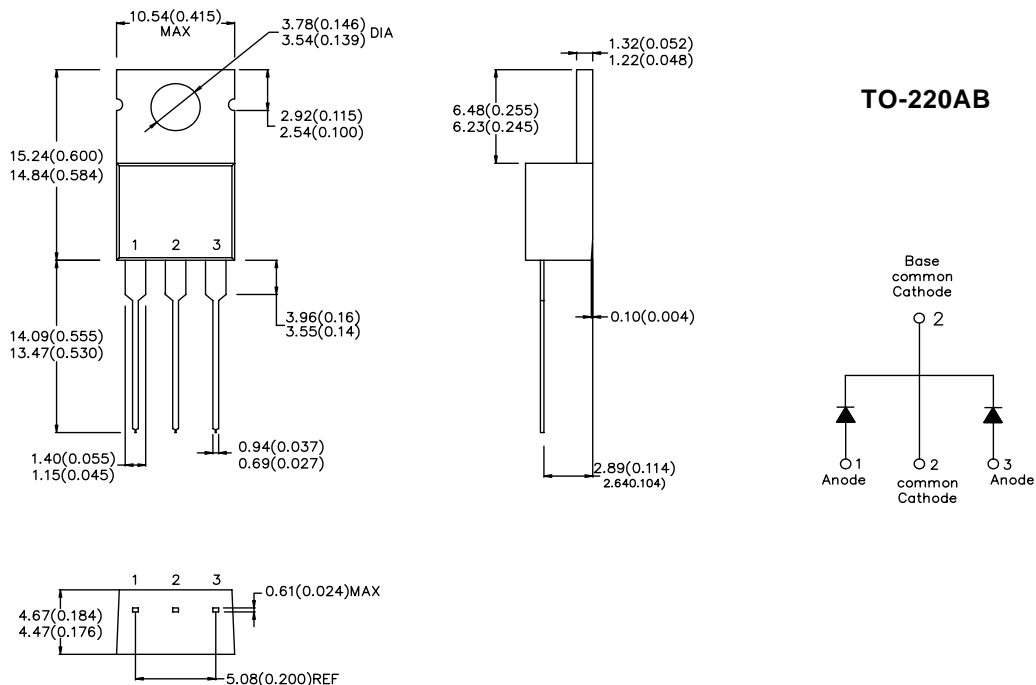
- Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

Features:

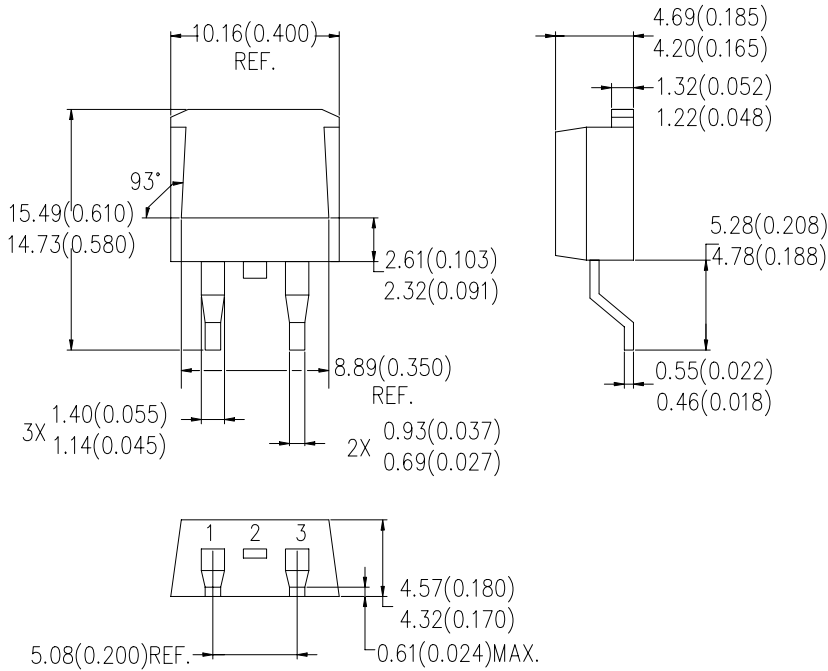
- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability

Case styles		
MBR2535CT MBR2545CT	MBRB2535CT MBRB2545CT	MBR2535CT-1 MBR2545CT-1
		
TO-220AB	D²PAK	TO-262

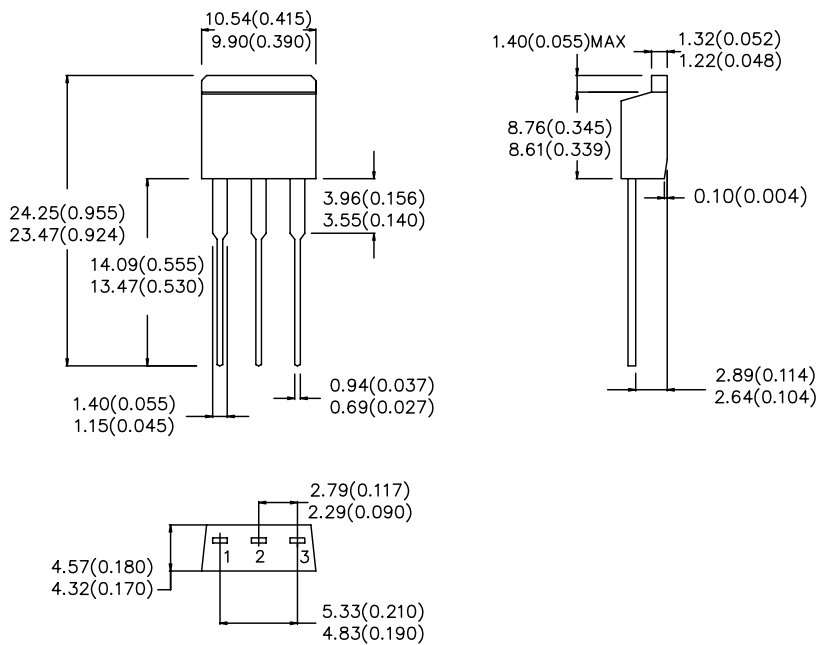
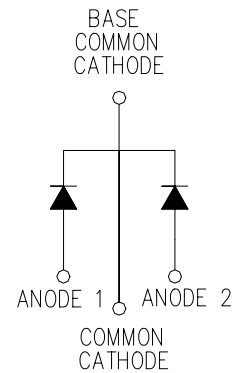
Mechanical Dimensions: In Inches / mm



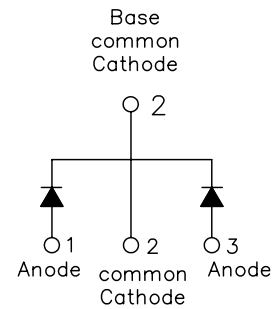
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D²PAK



TO-262



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Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	35	V
			45	
			MBR2535CT MBRB2535CT MBR2535CT-1	
			MBR2545CT MBRB2545CT MBR2545CT-1	
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 130\text{ }^\circ\text{C}$, rectangular wave form	15 (per leg) 30 (per device)	A
Peak Repetitive Forward Current (pre leg)	I_{FRM}	Rated V_R , square wave, 20kHz, $T_C = 130\text{ }^\circ\text{C}$	20	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A
Peak Repetitive Reverse Surge Current	I_{RRM}	2.0 μsec 1.0 kHz	1.0	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 30 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.82	V
	V_{F2}	@ 30 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.73	V
Max. Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$, Pulse $T_J = 25\text{ }^\circ\text{C}$	0.2	mA
	I_{R2}	@ $V_R = \text{rated } V_R$, Pulse $T_J = 125\text{ }^\circ\text{C}$	40	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$, $V_{SIG} = 50\text{ mV (p-p)}$	700	pF
Typical Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change (Rated V_R)	dv/dt	-	10,00	V/ μs

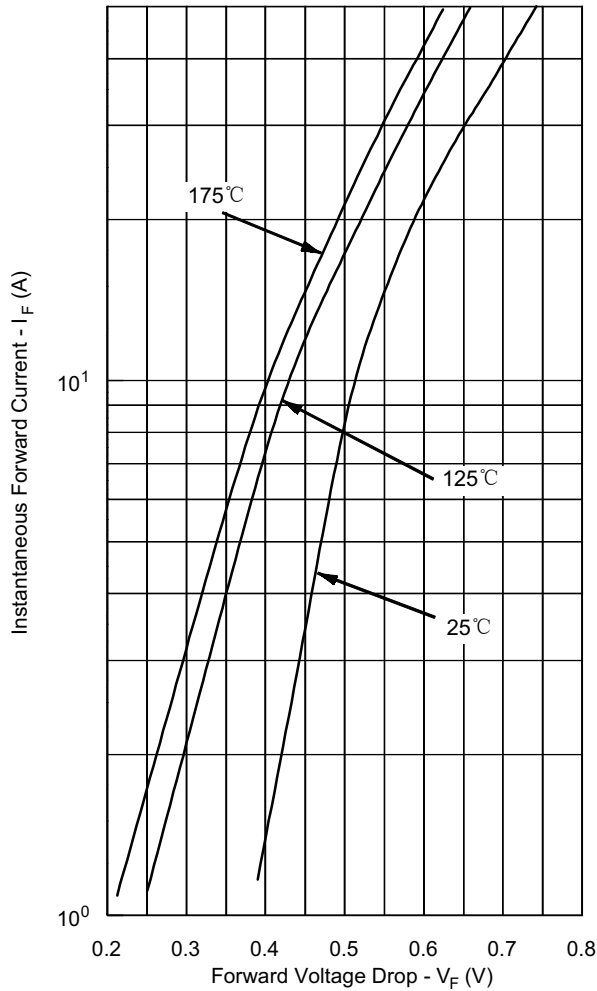
* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

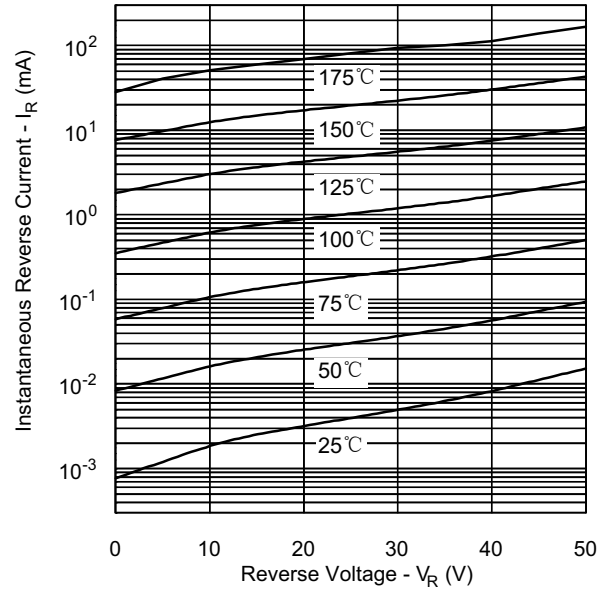
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-65 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-65 to +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	2.0	$^\circ\text{C/W}$
Maximum Thermal Resistance, Case to Heat Sink	$R_{\theta CS}$	Mounting surface, smooth and greased (only for TO-220)	0.5	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Mounting Torque	T_M	-	6(Min.) 12(Max.)	Kg-cm
Case Style	TO-220AB D ² PAK TO-262 (Suffix "-1" for TO-262,"MBRB x" for D ² PAK)			

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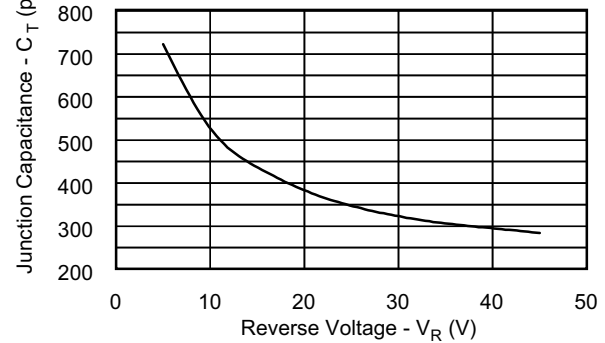
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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